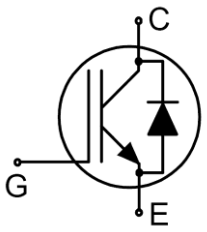
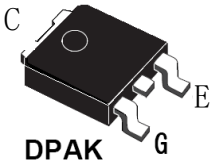
JT05N065RAD

主要参数 MAIN CHARACTERISTICS

I_C	5 A
V_{CES}	650V
$V_{cesat-typ}$（V_{ge}=15V）	1.7V

封装 **Package**





DPAK

用途

- 逆变器
- PDP
- UPS 电源
- 电机控制

APPLICATIONS

- General purpose inverters
- PDP
- UPS
- Motor Control

产品特性

- 低栅极电荷
- FS 技术,
- RoHS 产品

FEATURES

- Low gate charge
- FS Technology,
- RoHS product

订货信息 ORDER MESSAGE

订 货 型 号 Order codes				印 记 Marking	封 装 Package
有卤-条管 Halogen-Tube	无卤-条管 Non halogen-Tube	有卤-编带 Halogen-Reel	无卤-编带 Non halogen-Reel		
JT05N065RAD-R-B	JT05N065RAD-R-BR	JT05N065RAD-R-A	JT05N065RAD-R-AR	JT05N065RAD	DPAK

绝对最大额定值 ABSOLUTE RATINGS (Tc=25℃)

项 目 Parameter	符 号 Symbol	数 值 Value	单 位 Unit
最高集电极－发射极直流电压 Collector-Emmiter Voltage	V_{ces}	650	V
*连续集电极电流 Collector Current-continuous	I_C	10 (T=25℃)	A
		5(T=100℃)	A
最大脉冲集电极极电流（注 1） Collector Current – pulse （note 1）	I_{CM}	20	A
最高栅极发射极电压 Gate-Emmiter Voltage	V_{GES}	±30	V
安全工作区电流 Turn-off safe area	-	20	A
耗散功率 Power Dissipation	P_D T_C=25℃	59.5	W
最高结温及存储温度 Operating and Storage Temperature Range	T_J，T_{STG}	-55～+150	℃
引线最高焊接温度 Maximum Lead Temperature for Soldering Purposes	T_L	300	℃

*连续集电极电流由最高结温限制

*Collector current limited by maximum junction temperature

电特性 ELECTRICAL CHARACTERISTICS

项　　目 Parameter	符　号 Symbol	测试条件 Tests conditions	最小 Min	典型 Typ	最大 Max	单　位 Units
关态特性 Off –Characteristics						
集电极－发射极击穿电压 Collector-Emmiter Voltage	BV_{CES}	I_C=250μA, V_{GE}=0V	650	-	-	V
击穿电压温度特性 Breakdown Voltage Temperature Coefficient	$\Delta BV_{CES}/\Delta T_J$	I_C=1mA, referenced to 25℃	-	0.5	-	V/℃
零栅压下集电极漏电流 Zero Gate Voltage Collector Current	I_{CES}	V_{CE}=650V, V_{GE}=0V, T_C=25℃	-	-	10	μA
正向栅极体漏电流 Gate-body leakage current, forward	I_{GESF}	V_{CE}=0V, V_{GE} =20V	-	-	200	nA
反向栅极体漏电流 Gate-body leakage current, reverse	I_{GESR}	V_{CE}=0V, V_{GE} =-20V	-	-	-200	nA
通态特性 On-Characteristics						
阈值电压 Gate Threshold Voltage	$V_{GE(th)}$	V_{CE} = V_{GE} , I_C=250μA	4.5	-	6.5	V
饱和压降 Collector-Emmiter saturation Voltage	V_{CESAT}	V_{GE}=15V I_C=5A Tc=25℃	-	1.7	2.05	V
动态特性 Dynamic Characteristics						
输入电容 Input capacitance	C_{ies}	V_{CE}=25V, V_{GE}=0V, f=1.0MHz	-	289	-	pF
输出电容 Output capacitance	C_{oes}		-	32.7	-	pF
反向传输电容 Reverse transfer capacitance	C_{res}		-	7.4	-	pF
栅极电荷总量 Total Gate Charge	Qg	V_{CC}=400V,I_c=5A,R_G=10Ω V_{GE}=15 V T_C=25℃	-	11.8	-	nC
栅极-发射极电荷 Gate to emitter charge	Qge		-	2.57	-	
栅极-集电极电荷 Gate to collector charge	Qgc		-	5.1	-	
栅极电阻-Gate resistance	Rg	f=1 MHz, open collector	-	1.6	-	Ω
短路电流-short current	Isc	V_{GE}=15V V_{CE}=400V	-	30	-	A

电特性 ELECTRICAL CHARACTERISTICS

开关特性 Switching Characteristics						
项　　目 Parameter	符　号 Symbol	测试条件 Tests conditions	最小 Min	典型 Typ	最大 Max	单　位 Units
开启延迟时间 Turn-On delay time	$t_d(on)$	V_{CC}=400V,I_c=5A,R_G=60Ω V_{GE}=15 V T_C=25℃	-	22	-	ns
上升时间 Turn-On rise time	t_r		-	13	-	ns
关断延迟时间 Turn-Off delay time	$t_d(off)$		-	91	-	ns
下降时间 Turn-Off Fall time	t_f		-	25	-	ns
开通损耗 Turn-On energy	Eon		-	123	-	μJ
关断损耗 Turn-off energy	Eoff		-	53	-	μJ
总开关损耗 Total switching energy	Etot		-	176	-	μJ
反并联二极管特性及最大额定值 Anti-Parallel Diode Characteristics and Maximum Ratings						
正向压降 Drain-Source Diode Forward Voltage	V_F	V_{GE}=0V,　　I_F=5A	-	1.5	2.2	V
反向恢复时间 Diode Reverse recovery time	t_{rr}	V_{GE}=0V, V_R=400V I_F=5A dI_F/dt=200A/μs	-	33	-	ns
反向恢复电荷 Diode Reverse recovery charge	Qrr		-	145	-	nC
反向恢复电流 Diode Reverse recovery Current	I_{RRM}		-	2.7	-	A

项　　目 Parameter	符　号 Symbol	MAX	单　位 Unit
结到管壳的热阻 Thermal Resistance, Junction to Case	$R_{th(j-c)}$	2.1	℃/W
结到环境的热阻 Thermal Resistance, Junction to Ambient	$R_{th(j-A)}$	110	℃/W

注释：

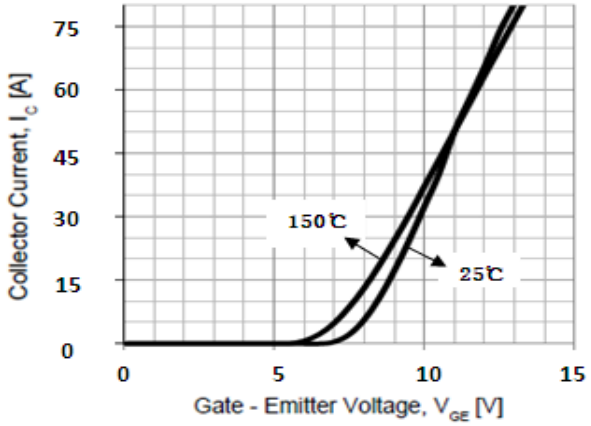
1：脉冲宽度由最高结温限制

Notes:

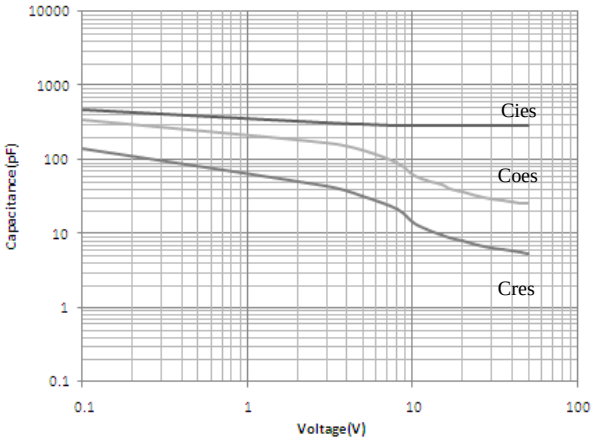
1：Pulse width limited by maximum junction temperature

特征曲线 ELECTRICAL CHARACTERISTICS (curves)

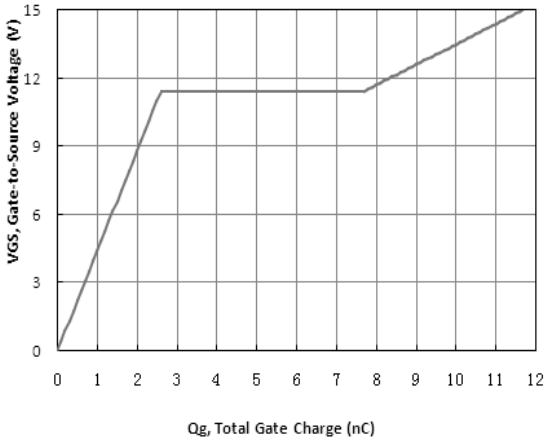
Typical Transfer Characteristics



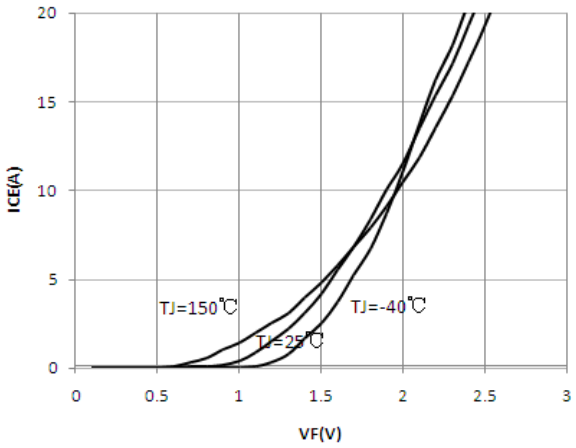
Capacitance Characteristics



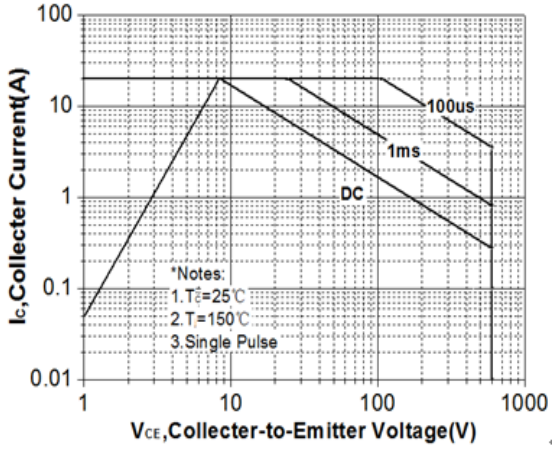
Gate Charge Characteristics



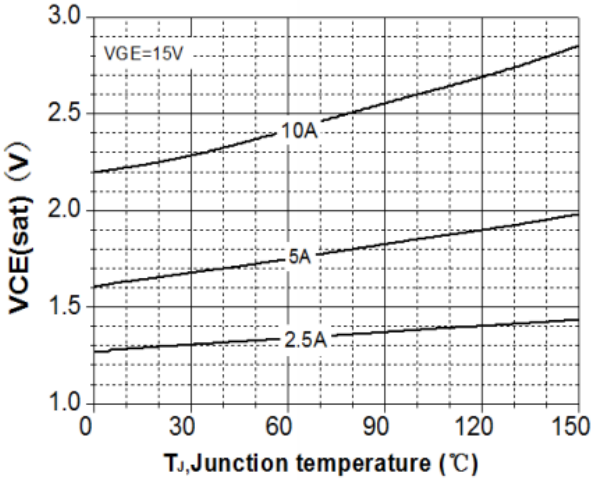
VF vs. Case Temperature at Variant Current Level



SOA Characteristics For DPAK

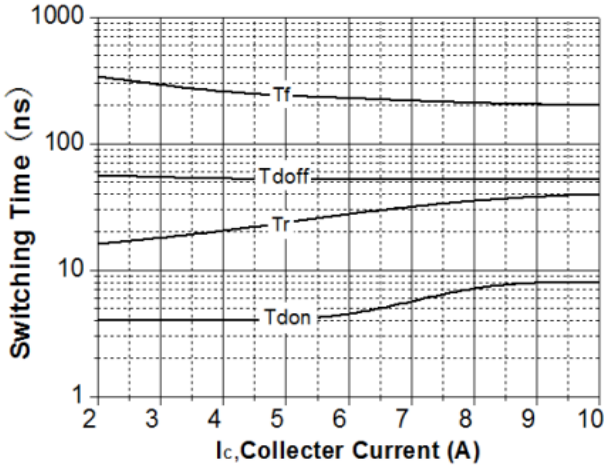


Vcesat vs Tj



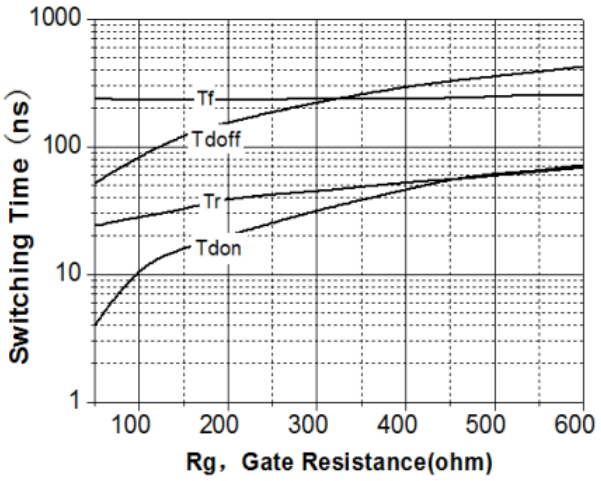
Switching Time vs Ic

Tj=150℃， Vge=15V, Vce=400V, Rg=60Ω



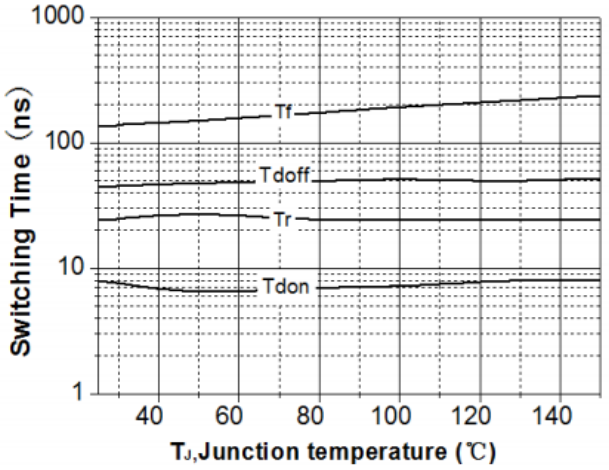
Switching Time vs Rg

Tj=150℃， Vge=15V, Vce=400V, Ic=5A



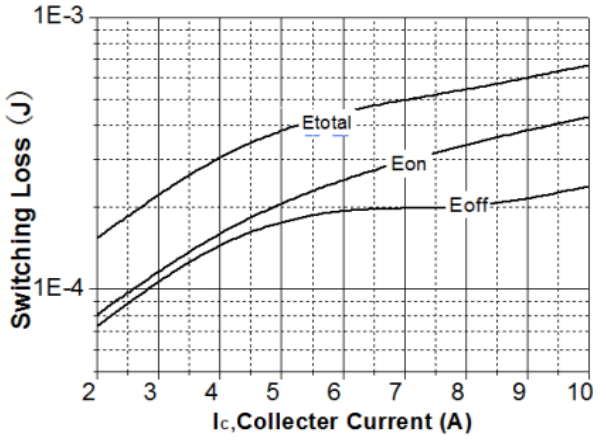
Switching Time vs Tj

Vge=15V, Vce=400V, Rg=60Ω, Ic=5A



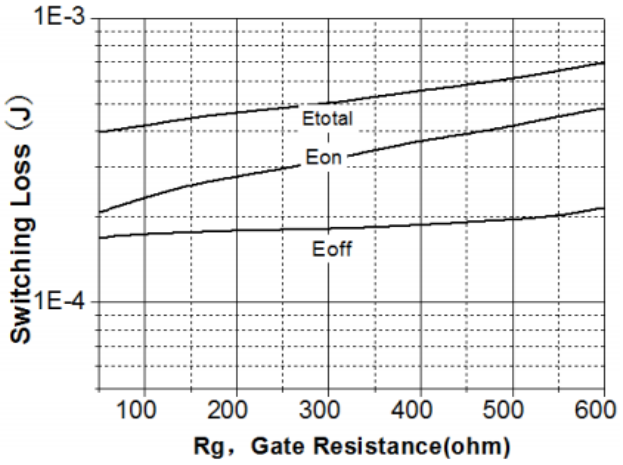
Switching Loss vs Ic

Tj=150℃, Vge=15V, Vce=400V, Rg=60Ω



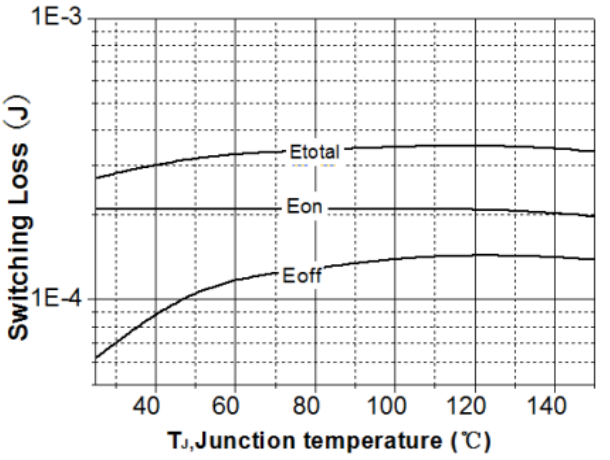
Switching Loss vs Rg

Tj=150℃, Vge=15V, Vce=400V, Ic=5A



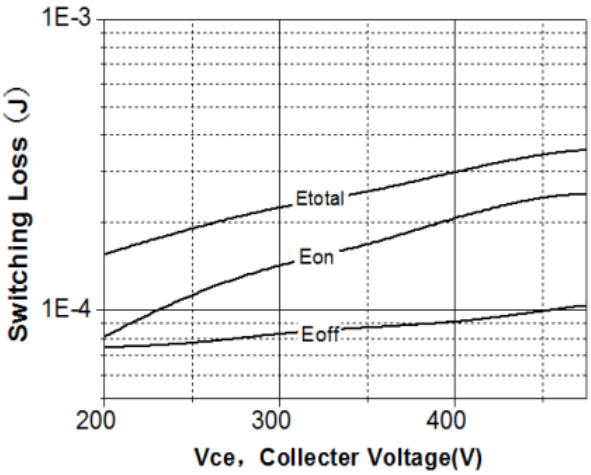
Switching Loss vs Tj

Vge=15V, Vce=400V, Ic=5A, Rg=60Ω

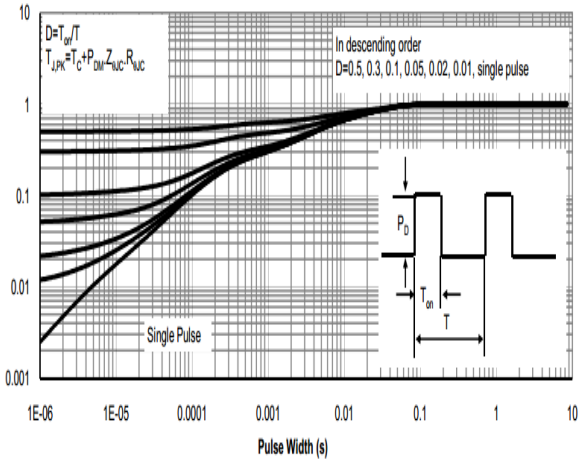


Switching Loss vs Vce

Tj=150℃， Vge=15V, Ic=5A, Rg=60Ω



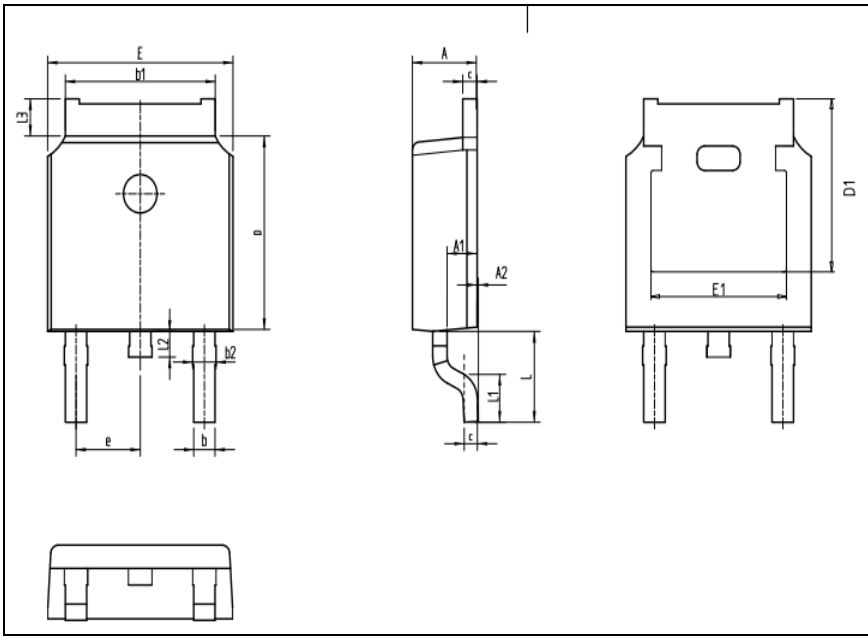
Transient Thermal Impedance



外形尺寸 **PACKAGE MECHANICAL DATA**

DPAK

单位 Unit：mm



SYMBOL	mm	
	MIN	MAX
A	2.16	2.41
A1	0.97	1.17
A2	0.00	0.15
b	0.63	0.93
b1	5.13	5.53
b2	0.66	0.96
c	0.40	0.60
D	5.80	6.40
D1	5.3REF	
E	6.30	6.90
E1	4.60	5.20
e	2.286BSC	
L	2.50	3.30
L1	1.20	1.80
L2	0.60	1.00
L3	0.85	1.30

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